

MOSFETs Silicon N-channel MOS (U-MOSIX-H)

# TK6R7P06PL

#### 1. Applications

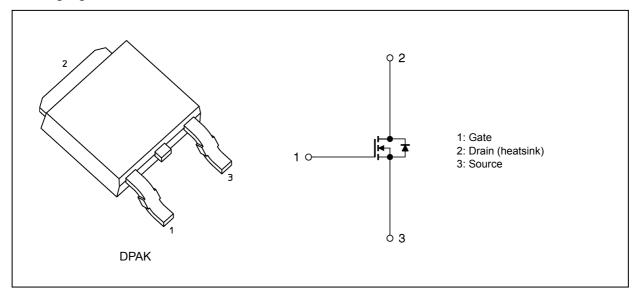
- · High-Efficiency DC-DC Converters
- · Switching Voltage Regulators
- · Motor Drivers

#### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 8.7 \text{ nC (typ.)}$
- (3) Small output charge:  $Q_{oss} = 23 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 5.0 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (5) Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 60 \text{ V)}$
- (6) Enhancement mode:  $V_{th} = 1.5$  to 2.5 V ( $V_{DS} = 10$  V,  $I_D = 0.3$  mA)

#### 3. Packaging and Internal Circuit

Toshiba Electronic Devices & Storage Corporation





### 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

| Characteristic                 | s                        |                    | Symbol           | Rating     | Unit |
|--------------------------------|--------------------------|--------------------|------------------|------------|------|
| Drain-source voltage           |                          |                    | $V_{DSS}$        | 60         | V    |
| Gate-source voltage            |                          |                    | $V_{GSS}$        | ±20        |      |
| Drain current (DC)             | (T <sub>c</sub> = 25 °C) | (Note 1)           | Ι <sub>D</sub>   | 46         | Α    |
| Drain current (DC)             | (Silicon limit)          | (Note 1), (Note 2) | $I_D$            | 74         |      |
| Drain current (pulsed)         | (t = 100 μs)             | (Note 1)           | I <sub>DP</sub>  | 190        |      |
| Power dissipation              | (T <sub>c</sub> = 25 °C) |                    | $P_D$            | 66         | W    |
| Single-pulse avalanche energy  |                          | (Note 3)           | E <sub>AS</sub>  | 14         | mJ   |
| Single-pulse avalanche current | ,                        | (Note 3)           | I <sub>AS</sub>  | 46         | Α    |
| Channel temperature            |                          |                    | T <sub>ch</sub>  | 175        | °C   |
| Storage temperature            |                          |                    | T <sub>stg</sub> | -55 to 175 | °C   |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

| Characteristics                    |                          | Symbol                | Max  | Unit |
|------------------------------------|--------------------------|-----------------------|------|------|
| Channel-to-case thermal resistance | (T <sub>c</sub> = 25 °C) | R <sub>th(ch-c)</sub> | 2.24 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note 2: Limited 46 A by package capability

Note 3:  $V_{DD}$  = 48 V,  $T_{ch}$  = 25 °C (initial), L = 5.3  $\mu H,\ I_{AS}$  = 46 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

### 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                         | Symbol               | Test Condition                                    | Min | Тур. | Max  | Unit |
|---|----------------------|---|-----|------|------|------|
| Gate leakage current                    | I <sub>GSS</sub>     | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _   | _    | ±0.1 | μА   |
| Drain cut-off current                   | I <sub>DSS</sub>     | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V     | _   | _    | 10   |      |
| Drain-source breakdown voltage          | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V     | 60  | _    | _    | ٧    |
| Drain-source breakdown voltage (Note 4) | V <sub>(BR)DSX</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V   | 45  | _    | _    |      |
| Gate threshold voltage                  | $V_{th}$             | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.3 mA   | 1.5 | _    | 2.5  |      |
| Drain-source on-resistance              | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 8 A     | _   | 7.5  | 11.1 | mΩ   |
|   |                      | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 23 A     | _   | 5.0  | 6.7  |      |

Note 4: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub> | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _   | 1990 |     | pF   |
| Reverse transfer capacitance   | $C_{rss}$        |  | _   | 45   | _   |      |
| Output capacitance             | C <sub>oss</sub> |  | _   | 350  | _   |      |
| Gate resistance                | r <sub>g</sub>   | _  | _   | 2.0  | _   | Ω    |
| Switching time (rise time)     | t <sub>r</sub>   | See Fig. 6.2.1   | _   | 5    | _   | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>  |  | _   | 16   | _   |      |
| Switching time (fall time)     | t <sub>f</sub>   |  | _   | 10   | _   |      |
| Switching time (turn-off time) | t <sub>off</sub> |  | _   | 35   | _   |      |

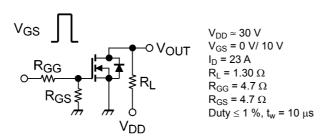


Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                     | Symbol           | Test Condition  | Min | Тур. | Max | Unit |
|-------------------------------------|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus | $Q_g$            | $V_{DD} \approx 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 23 \text{ A}$    | _   | 26   | _   | nC   |
| gate-drain)                         |                  | $V_{DD} \approx 30 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 23 \text{ A}$ | _   | 13   | _   |      |
| Gate-source charge 1                | Q <sub>gs1</sub> | $V_{DD} \approx 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 23 \text{ A}$    | _   | 7.9  | _   |      |
| Gate-drain charge                   | $Q_{gd}$         |   | _   | 4.6  | _   |      |
| Gate switch charge                  | $Q_{SW}$         |   | _   | 8.7  | _   |      |
| Output charge                       | $Q_{oss}$        | $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$            | _   | 23   | _   |      |



### 6.4. Source-Drain Characteristics ( $T_a = 25$ °C unless otherwise specified)

| Characteristics                         | Symbol                           | Test Condition                                   | Min | Тур. | Max  | Unit |
|---|----------------------------------|--|-----|------|------|------|
| Reverse drain current (pulsed) (Note 5) | I <sub>DRP</sub><br>(t = 100 μs) |  | ı   | ı    | 190  | Α    |
| Diode forward voltage                   | V <sub>DSF</sub>                 | I <sub>DR</sub> = 46 A, V <sub>GS</sub> = 0 V    |     |      | -1.5 | V    |
| Reverse recovery time                   | t <sub>rr</sub>                  | I <sub>DR</sub> = 11.5 A, V <sub>GS</sub> = 0 V, | _   | 31   |      | ns   |
| Reverse recovery charge                 | Q <sub>rr</sub>                  | -dI <sub>DR</sub> /dt = 100 A/μs                 | _   | 25   | _    | nC   |

Note 5: Ensure that the channel temperature does not exceed 175 °C.

### 7. Marking

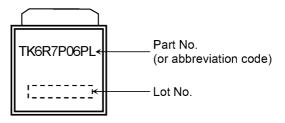


Fig. 7.1 Marking



#### 8. Characteristics Curves (Note)

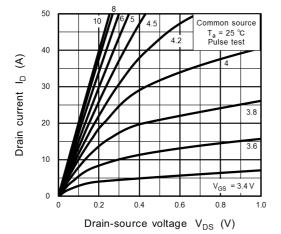
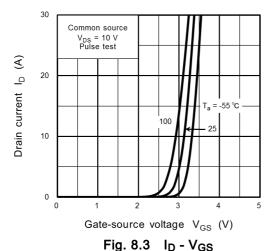


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>



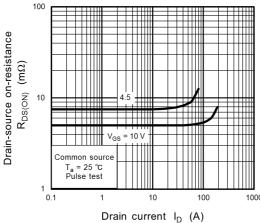


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

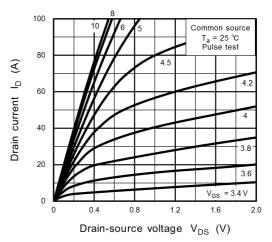


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

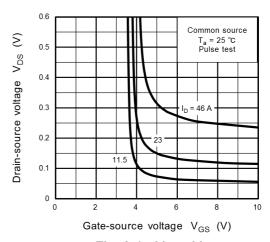


Fig. 8.4 VDS - VGS

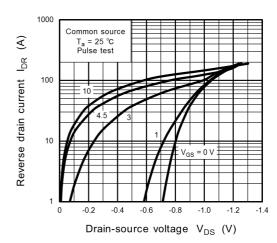


Fig. 8.6 IDR - VDS



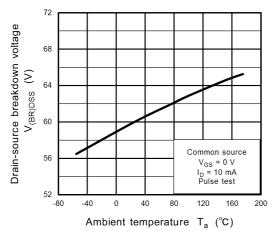


Fig. 8.7 V<sub>(BR)DSS</sub> - T<sub>a</sub>

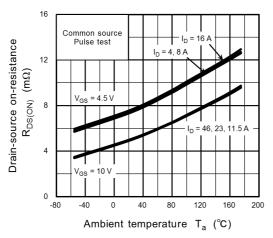


Fig. 8.9 R<sub>DS(ON)</sub> - T<sub>a</sub>

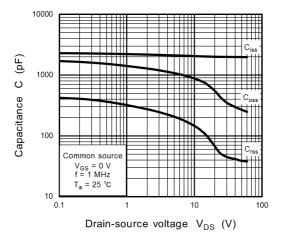


Fig. 8.11 Capacitance - V<sub>DS</sub>

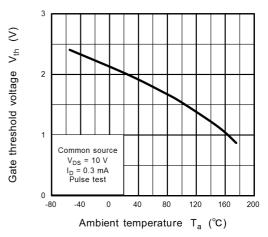


Fig. 8.8 V<sub>th</sub> - T<sub>a</sub>

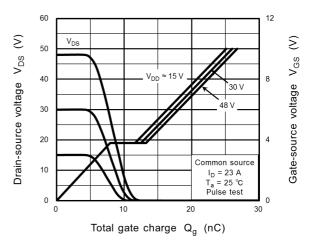


Fig. 8.10 Dynamic Input/Output Characteristics

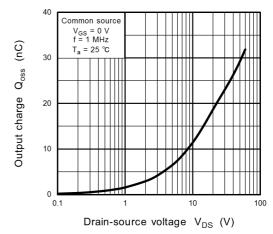


Fig. 8.12 Qoss - VDS



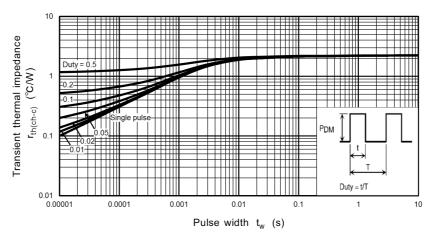
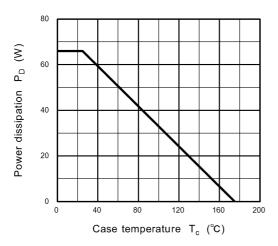


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)



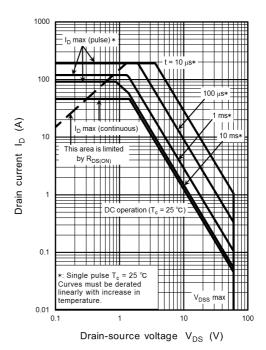


Fig. 8.14 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

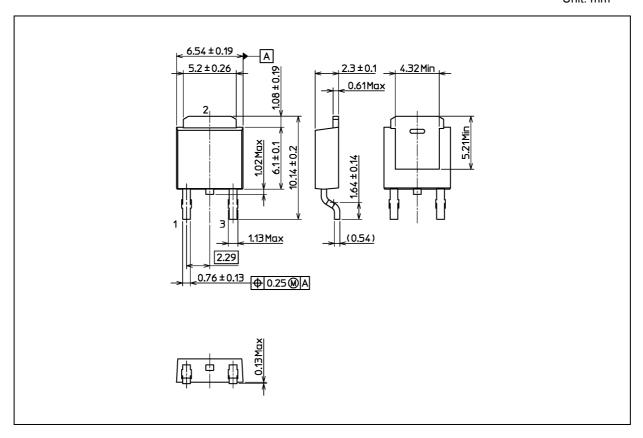
Fig. 8.15 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### **Package Dimensions**

Unit: mm



Weight: 0.33 g (typ.)

|                 | Package Name(s) |
|-----------------|-----------------|
| TOSHIBA: 2-7N1S |                 |
| Nickname: DPAK  |                 |



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